# JSR Lift off Photoresist LP series

## Single Layer Lift off resist

#### Single Layer (Negative tone)



LP-0008

Thickness: 2.5 - 4.0 µm

Simple process

#### **Lift-off process**

Lithography



Stripping







## Ideal cross-section profile

- \* Deep undercut shape can be easily obtained
- Simple and stable lithography process
  - \* One step exposure and good PCD/PED stability
- **Good stripping property** 
  - \* Easily removed by various solvent
- **Excellent thermal tolerance** 
  - \* PR profile was not changed after thermal treatment at 100 °C

## LP-0008 Patterning Profile

### **Exposure dose**

230 mJ/cm<sup>2</sup>

240 mJ/cm<sup>2</sup>

250 mJ/cm<sup>2</sup>

0.8 µm

260 mJ/cm<sup>2</sup>

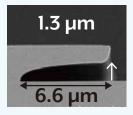
270 mJ/cm

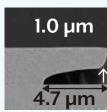
50 sec.

60 sec.

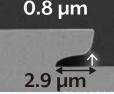
**Developing time** 

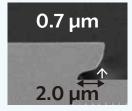
70 sec.

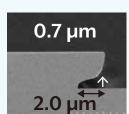


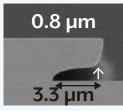












Film Thickness: 2.5 µm L/S: 20 µm / 20 µm

